

Silicon TVS Diode

- ESD / transient protection of data and power lines in low voltage applications according to: IEC61000-4-2 (ESD): ± 25 kV (air) 20 kV (contact) IEC61000-4-4 (EFT): 50 A / 2.5 kV (5/50 ns) IEC61000-4-5 (surge): 5.5 A / 80 W (8/20 μs)
- Small form factor (0402 inch): 1.0 x 0.6 x 0.4 mm³
- Bi-directional, symmetrical working voltage up to ± 5.3 V
- Ultralow and symmetric clamping voltage
- \bullet Ultralow dynamic resistance $\textbf{0.4}~\Omega$
- Very fast response time
- Pb-free (RoHS compliant) package

Applications

Recommended to protect audio lines / microphone lines / speaker and headset systems in:

- Mobile phones
- Mobile TV
- Set top boxes
- MP3 players
- Minidisc players
- Portable entertainment electronics



ESD5V3S1B-02LRH



Туре	Package	Configuration	Marking
ESD5V3S1B-02LRH	TSLP-2-17	1 line, bi-directional	E1





Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit				
ESD air / contact discharge ¹⁾	V _{ESD}	25 / 20	kV				
Peak pulse current ($t_p = 8 / 20 \ \mu s$) ²⁾	I _{pp}	5.5	A				
Peak pulse power ($t_p = 8 / 20 \ \mu s^{2}$)	P _{pk}	80	W				
Operating temperature range	T _{op}	-55125	°C				
Storage temperature	T _{stg}	-65150					

Electrical Characteristics at $T_A = 25^{\circ}C$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.]
Characteristics	·				
Reverse working voltage	V _{RWM}	-5.3	-	5.3	V
Breakdown voltage	V _(BR)	6	-	-	
l _(BR) = 1 mA					
Reverse current	I _R	-	-	0.1	μA
V _R = 3.3 V					
Clamping voltage	V _{CL}				V
$I_{\rm PP}$ = 1 A, $t_{\rm p}$ = 8/20 µs ²⁾		-	8	10	
$I_{\rm PP}$ = 3.5 A, $t_{\rm p}$ = 8/20 µs ²)		-	10	12	
$I_{\rm PP} = 5.5 \text{ A}, \ t_{\rm p} = 8/20 \ \mu s^{2}$		-	11	13	
Diode capacitance	CT				pF
V _R = 0 V, <i>f</i> = 1 MHz		-	17.5	20	
V _R = 2.5 V, <i>f</i> = 1 MHz		-	14.5	-	
Dynamic resistance ³⁾ (t_p = 30 ns)	R _D	-	0.4	-	Ω

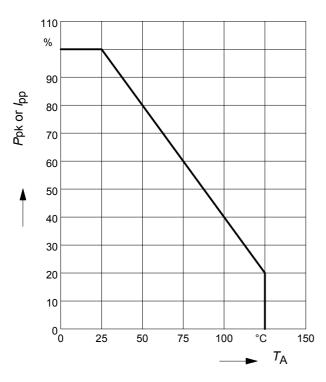
 $^{1}V_{\text{ESD}}$ according to IEC61000-4-2

 $^2\textit{I}_{pp}$ according to IEC61000-4-5

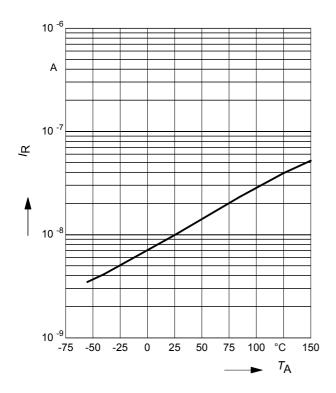
³ according to TLP tests



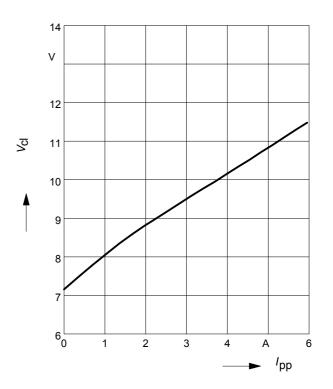
Power derating curve $P_{pk} = f(T_A)$



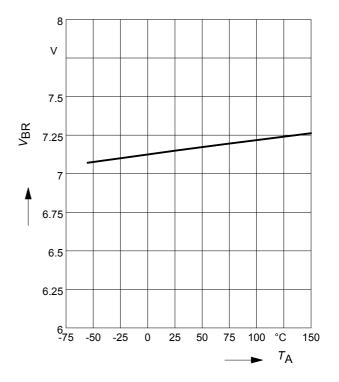
Reverse current $I_R = f(T_A)$ $V_R = 3.3 V$



Clamping voltage, $V_{cl} = f(I_{pp})$ $t_p = 8 / 20 \ \mu s$



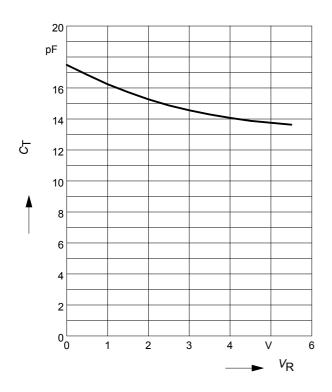
Breakdown voltage $V_{BR} = f(T_A)$ $I_R = 1 \text{ mA}$





Diode capacitance $C_{T} = f (V_{R})$

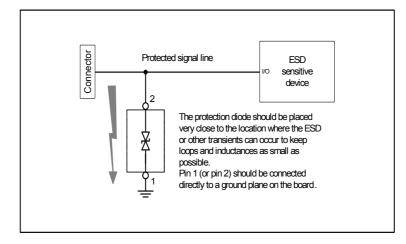
f = 1 MHz



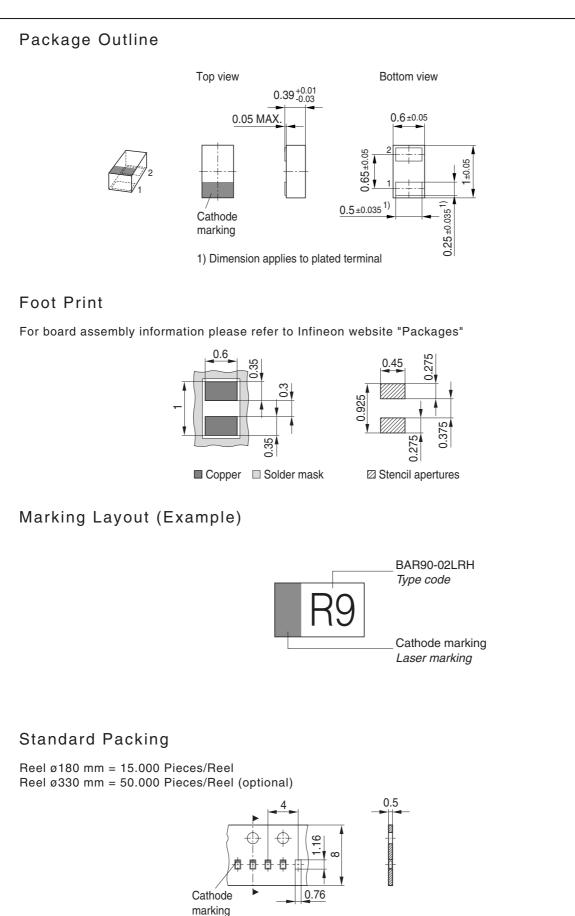


Application example

single channel, bi-directional









Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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